



Docket No.: R2180.0190/P190
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Takaaki Negoro et al.

Application No.: 10/780,699

Confirmation No.: 2014

Filed: February 19, 2004

Art Unit: 2814

For: Metal oxide silicon transistor and semiconductor
apparatus having high lambda and beta
performances

Examiner: P. X. Cao

PLEASE
ENTER AMENDMENT
PC
A/23/07

AMENDMENT AFTER FINAL ACTION UNDER 37 C.F.R. 1.116

MS AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated January 4, 2007, finally rejecting claim 1, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 4 of this paper.